

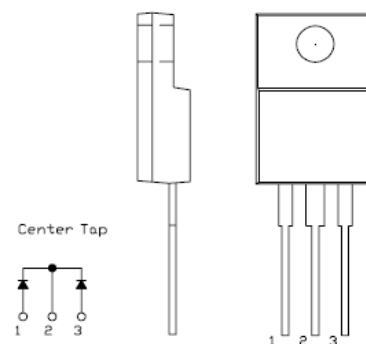
MBRF20100CT SCHOTTKY RECTIFIER

Applications:

- Switching power supply
- Converters
- Free-Wheeling diodes
- Reverse battery protection

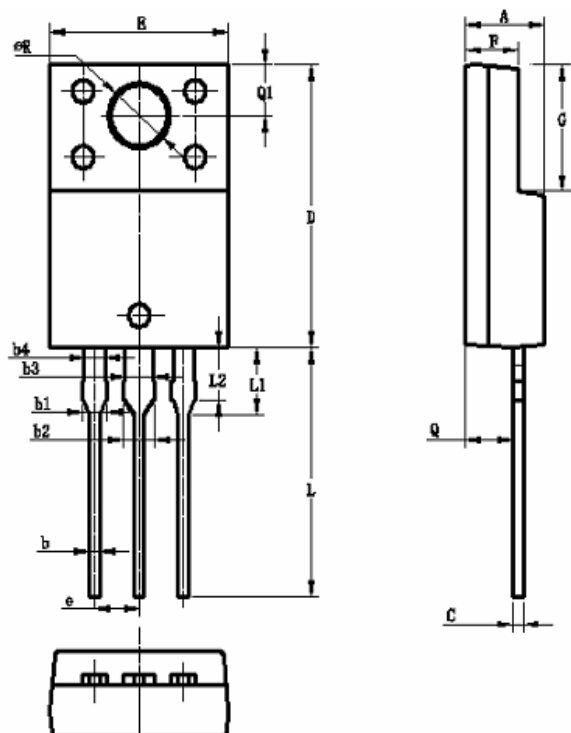
Features:

- 175 °C T_J operation
- Center tap configuration
- Low forward voltage drop
- High purity, high temperature epoxy encapsulation for enhanced mechanical strength and moisture resistance
- High frequency operation
- Guard ring for enhanced ruggedness and long term reliability
- This is a Pb – Free Device
- All SMC parts are traceable to the wafer lot
- Additional testing can be offered upon request



OUTLINE DRAWING

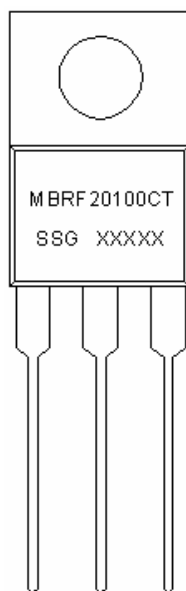
Mechanical Dimensions (In mm)



	OPTION 1(CJ)		OPTION 2(HD)	
Dim	Min	Max	Min	Max
A	4.35	4.65	4.30	4.70
b	0.50	0.75	0.50	0.75
b1	1.15	1.402	1.20	1.45
b2	1.55	1.802	1.60	1.85
b3	1.55	1.65	1.50	1.75
b4	1.10	1.35	1.10	1.35
C	0.50	0.75	0.55	0.75
D	14.8	15.2	14.80	15.20
E	10.06	10.26	9.96	10.36
e	2.46	2.62	2.55TYP	
F	2.85	3.15	2.80	3.20
G	6.50	6.90	6.50	6.90
L	12.70	13.70	12.70	13.70
L1	3.40	3.80	3.40	4.00
L2	2.60	3.00	-	-
Q	2.60	2.80	2.50	2.90
Q1	2.50	2.90	2.50	2.90
ØR	3.40	3.60	3.30	3.70

ITO-220AB

Marking Diagram:



Where XXXXX is YYWWL

MBR = Device Type
 F = Package type
 20 = Forward Current (20A)
 100 = Reverse Voltage (100V)
 CT = Configuration
 SSG = SSG
 YY = Year
 WW = Week
 L = Lot Number

Cautions: Molding resin
Epoxy resin UL:94V-0

Ordering Information:

Device	Package	Shipping
MBRF20100CT	ITO-220AB (Pb-Free)	50pcs / tube

For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specification.

Maximum Ratings:

Characteristics	Symbol	Condition	Max.	Units
Peak Inverse Voltage	V_{RWM}	-	100	V
Max. Average Forward Current	$I_{F(AV)}$	50% duty cycle @ $T_C = 133^\circ\text{C}$, rectangular wave form	10(Per leg) 20(Per device)	A
Max. Peak One Cycle Non-Repetitive Surge Current (per leg)	I_{FSM}	8.3 ms, half Sine pulse	150	A

Electrical Characteristics:

Characteristics	Symbol	Condition	Max.	Units
Max. Forward Voltage Drop (per leg)*	V _{F1}	@ 5A, Pulse, T _J = 25 °C	0.80	V
	V _{F2}	@ 10A, Pulse, T _J = 25 °C	0.90	
		@ 5A, Pulse, T _J = 125 °C	0.70	V
		@ 10A, Pulse, T _J = 125 °C	0.80	
Max. Reverse Current at DC condition (per leg)	I _{R1}	@V _R = rated V _R T _J = 25 °C	1.0	mA
Max. Reverse Current (per leg)*	I _{R2}	@V _R = rated V _R T _J = 125 °C	6.0	mA
Repetitive peak reverse current	I _{RRM}	tp = 2 μs square F= 1 kHz	1	A
Max. Junction Capacitance (per leg)	C _T	@V _R = 5V, T _C = 25 °C f _{sig} = 1MHz	250	pF
Typical Series Inductance (per leg)	L _S	Measured lead to lead 5 mm from package body	8.0	nH
Max. Voltage Rate of Change	dv/dt	-	10,000	V/μs
RSM Isolation Voltage (t = 1.0 second, R. H. < =30%, T _A = 25 °C)	V _{ISO}	Clip mounting, the epoxy body away from the heatsink edge by more than 0.110" along the lead direction.	4500	V
		Clip mounting, the epoxy body is inside the heatsink.	3500	
		Screw mounting, the epoxy body is inside the heatsink.	1500	

* Pulse Width < 300μs, Duty Cycle <2%

Thermal-Mechanical Specifications:

Characteristics	Symbol	Condition	Specification	Units
Max. Junction Temperature	T _J	-	-55 to +175	°C
Max. Storage Temperature	T _{stg}	-	-55 to +175	°C
Maximum Thermal Resistance Junction to Case (per leg)	R _{θJC}	DC operation	3.5	°C/W
Approximate Weight	wt	-	2	g
Case Style	ITO-220AB			

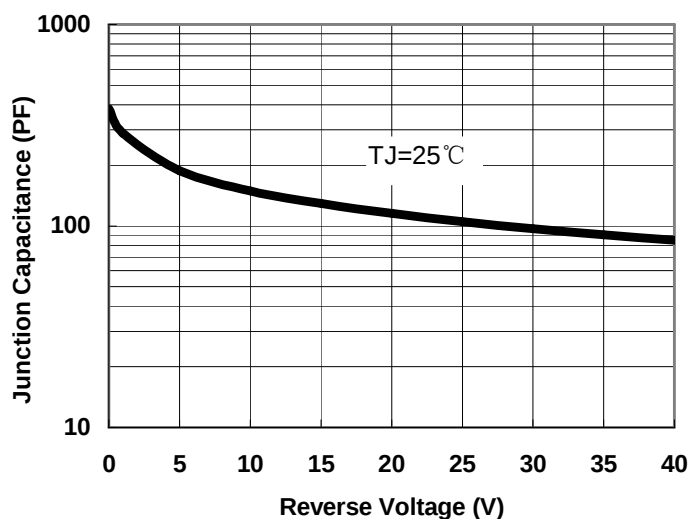


Fig.1-Typical Junction Capacitance

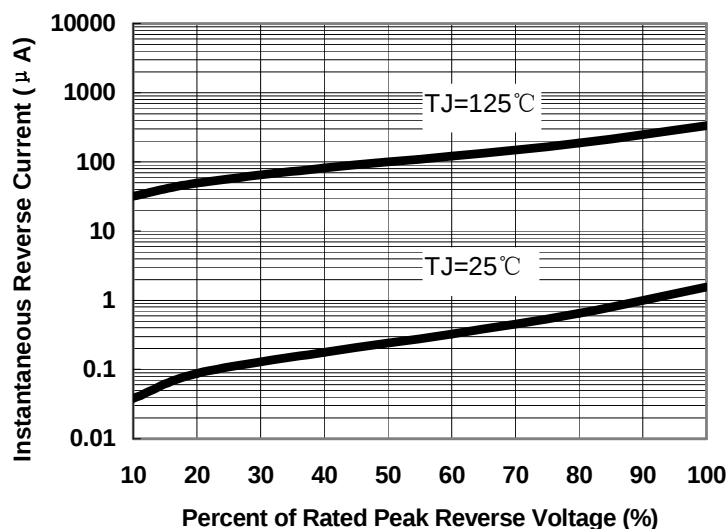


Fig.2-Typical Reverse Characteristics

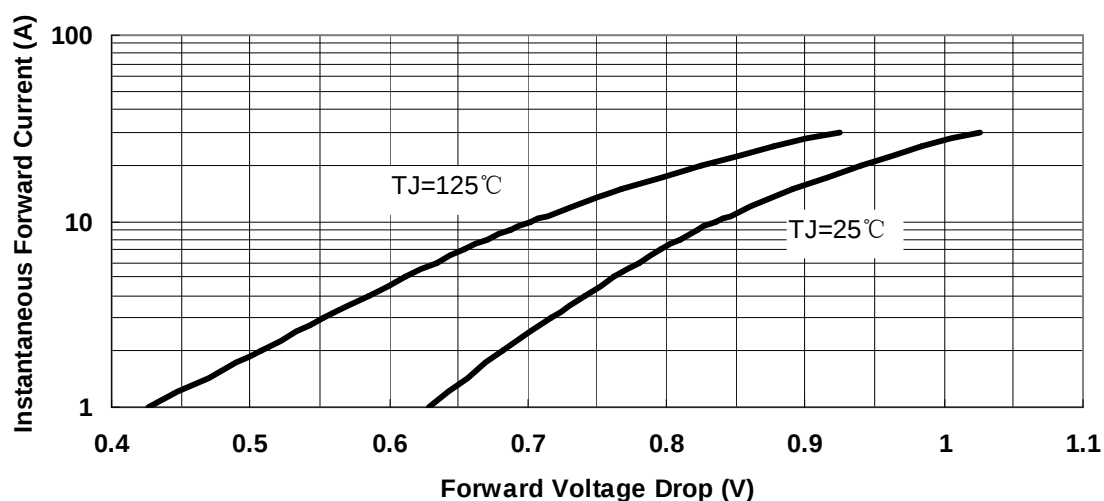


Fig.3-Typical Instantaneous Forward Voltage Characteristics

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